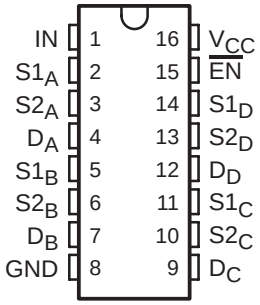
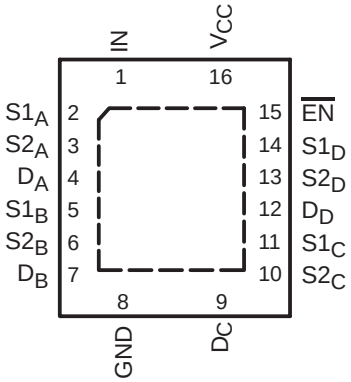
- **Low Differential Gain and Phase (D_G = 0.2%, D_P = 0.1° Typ)**
- **Wide Bandwidth (B_W = 500 MHz Typ)**
- **Low Crosstalk (X_{TALK} = −80 dB Typ)**
- **Bidirectional Data Flow, With Near-Zero Propagation Delay**
- **Low and Flat ON-State Resistance (r_{on} = 3 Ω Typ, $r_{on(flat)}$ = 1 Ω Typ)**
- **V_{CC} Operating Range From 3 V to 3.6 V**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Data and Control Inputs Provide Undershoot Clamp Diode**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2000-V Human-Body Model (A114-B, Class II)**
  - **1000-V Charged-Device Model (C101)**
- **Suitable for Both RGB and Composite Video Switching**

D, DBQ, DGV, OR PW PACKAGE
(TOP VIEW)



RGY PACKAGE
(TOP VIEW)



description/ordering information

The TI video switch TS3V340 is a 4-bit 1-of-2 multiplexer/demultiplexer with a single switch-enable ($\overline{EN}$) input. When $\overline{EN}$ is low, the switch is enabled, and the D port is connected to the S port. When $\overline{EN}$ is high, the switch is disabled, and the high-impedance state exists between the D and S ports. The select (IN) input controls the data path of the multiplexer/demultiplexer.

Low differential gain and phase makes this switch ideal for composite and RGB video applications. The device has a wide bandwidth and low crosstalk, making it suitable for high-frequency applications as well.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 85°C	QFN − RGY	Tape and reel	TS3V340RGYR	TF340
	SOIC − D	Tube	TS3V340D	TS3V340
		Tape and reel	TS3V340DR	
	SSOP (QSOP) − DBQ	Tape and reel	TS3V340DBQR	TF340
	TSSOP − PW	Tube	TS3V340PW	TF340
		Tape and reel	TS3V340PWR	
	TVSOP − DGV	Tape and reel	TS3V340DGVR	TF340

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

description/ordering information (continued)

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. This switch maintains isolation during power off.

To ensure the high-impedance state during power up or power down, $\overline{EN}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

FUNCTION TABLE

INPUTS		INPUT/OUTPUT D	FUNCTION
$\overline{EN}$	IN		
L	L	S1	D port = S1 port
L	H	S2	D port = S2 port
H	X	Z	Disconnect

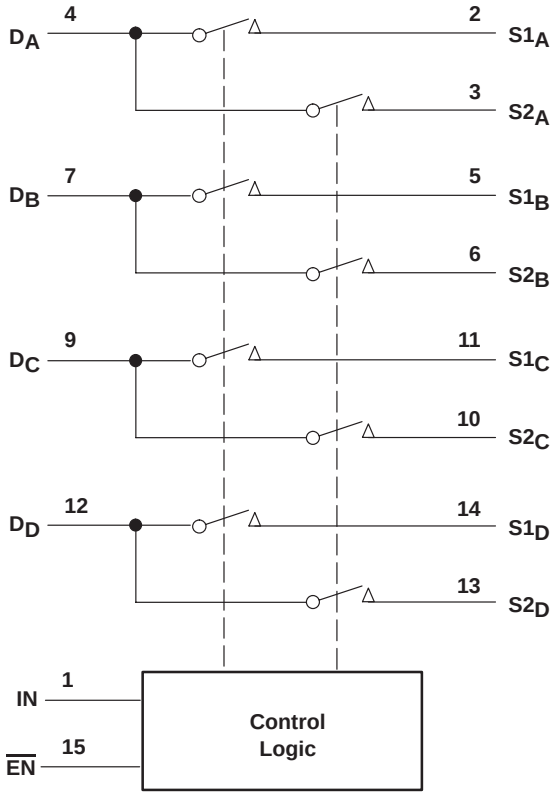
PIN DESCRIPTION

PIN NAME	DESCRIPTION
S1, S2	Analog video I/Os
D	Analog video I/Os
IN	Select input
$\overline{EN}$	Switch-enable input

PARAMETER DEFINITIONS

PARAMETER	DESCRIPTION
R_{ON}	Resistance between the D and S ports, with the switch in the ON state
I_{OZ}	Output leakage current measured at the D and S ports, with the switch in the OFF state
I_{OS}	Short-circuit current measured at the I/O pins
V_{IN}	Voltage at IN
V_{EN}	Voltage at $\overline{EN}$
C_{IN}	Capacitance at the control ($\overline{EN}$, IN) inputs
C_{OFF}	Capacitance at the analog I/O port when the switch is OFF
C_{ON}	Capacitance at the analog I/O port when the switch is ON
V_{IH}	Minimum input voltage for logic high for the control ($\overline{EN}$, IN) inputs
V_{IL}	Maximum input voltage for logic low for the control ($\overline{EN}$, IN) inputs
V_{IK}	I/O and control ($\overline{EN}$, IN) inputs diode clamp voltage
V_I	Voltage applied to the D or S pins when D or S is the switch input
V_O	Voltage applied to the D or S pins when D or S is the switch output
I_{IH}	Input high leakage current of the control ($\overline{EN}$, IN) inputs
I_{IL}	Input low leakage current of the control ($\overline{EN}$, IN) inputs
I_I	Current into the D or S pins when D or S is the switch input
I_O	Current into the D or S pins when D or S is the switch output
I_{off}	Output leakage current measured at the D or S ports, with V_{CC} = 0
t_{pds}	Propagation delay measured between $S1_X$ and $S2_X$ under the specified conditions, measured from 50% of the digital input to 90% of the analog output
B_W	Frequency response of the switch in the ON state, measured at −3 dB
X_{TALK}	Unwanted signal coupled from channel to channel. Measured in −dB. X_{TALK} = 20 log V_O/V_I. This is a nonadjacent crosstalk.
O_{IRR}	OFF isolation is the resistance (measured in −dB) between the input and output with the switch OFF.
D_G	Magnitude variation between analog input and output pins when the switch is ON and the DC offset of composite video signal varies at the analog input pin. In NTSC standard, the frequency of the video signal is 3.58 MHz, and DC offset is from 0 to 0.714 V.
D_P	Phase variation between analog input and output pins when the switch is ON and the DC offset of composite video signal varies at the analog input pin. In NTSC standard, the frequency of the video signal is 3.58 MHz, and DC offset is from 0 to 0.714 V.
I_{CC}	Static power-supply current
I_{CCD}	Variation of I_{CC} for a change in frequency in the control ($\overline{EN}$, IN) inputs
ΔI_{CC}	Increase in supply current for each control input that is at the specified voltage level, rather than V_{CC} or GND

functional diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . −0.5 V to 4.6 V
Control input voltage range, V_{IN} (see Notes 1 and 2) . . . . . −0.5 V to 7 V
Switch I/O voltage range, $V_{I/O}$ (see Notes 1, 2, and 3) . . . . . −0.5 V to 7 V
Control input clamp current, I_{IK} (V_{IN} < 0) . . . . . −50 mA
I/O port clamp current, $I_{I/OK}$ ($V_{I/O}$ < 0) . . . . . −50 mA
ON-state switch current, $I_{I/O}$ (see Note 4) . . . . . ±128 mA
Continuous current through V_{CC} or GND terminals . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 5): D package . . . . . 73°C/W
(see Note 5): DBQ package . . . . . 90°C/W
(see Note 5): DGV package . . . . . 120°C/W
(see Note 5): PW package . . . . . 108°C/W
(see Note 6): RGY package . . . . . 39°C/W
Storage temperature range, T_{stg} . . . . . −65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to ground, unless otherwise specified.
2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
3. V_I and V_O are used to denote specific conditions for $V_{I/O}$.
4. I_I and I_O are used to denote specific conditions for $I_{I/O}$.
5. The package thermal impedance is calculated in accordance with JESD 51-7.
6. The package thermal impedance is calculated in accordance with JESD 51-5.

recommended operating conditions (see Note 7)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	3	3.6	V
V_{IH}	High-level control input voltage ($\overline{EN}$, IN)	2	5.5	V
V_{IL}	Low-level control input voltage ($\overline{EN}$, IN)	0	0.8	V
V_O	Analog I/O voltage	0	5.5	V
T_A	Operating free-air temperature	−40	85	°C

NOTE 7: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)†

PARAMETER		TEST CONDITIONS				MIN	TYP‡	MAX	UNIT
V_{IK}	$\overline{EN}$, IN	V_{CC} = 3 V,	I_{IN} = −18 mA					−1.8	V
I_{IH}	$\overline{EN}$, IN	V_{CC} = 3.6 V,	V_{IN} and V_{EN} = 5.5 V					±1	µA
I_{IL}	$\overline{EN}$, IN	V_{CC} = 3.6 V,	V_{IN} and V_{EN} = GND					±1	µA
I_{OZ}§		V_{CC} = 3.6 V,	V_O = 0 to 5.5 V,	V_I = 0,	Switch OFF			±1	µA
I_{OS}¶		V_{CC} = 3.6 V,	V_O = 0.5 V_{CC},	V_I = 0,	Switch ON	50			mA
I_{off}		V_{CC} = 0,	V_O = 0 to 5.5 V,	V_I = 0				1	µA
I_{CC}		V_{CC} = 3.6 V,	$I_{I/O}$ = 0,	Switch ON or OFF			0.7	1.5	mA
ΔI_{CC}	$\overline{EN}$, IN	V_{CC} = 3.6 V,	One input at 3 V,	Other inputs at V_{CC} or GND				30	µA
I_{CCD}		V_{CC} = 3.6 V, D and S ports open,	V_{EN} = GND, V_{IN} input switching 50% duty cycle					0.35	mA/ MHz
C_{IN}	$\overline{EN}$, IN	V_{IN} or V_{EN} = 5.5 V,	3.3 V or 0,	f = 1 MHz			2.5	3.5	pF
C_{OFF}	D port	V_I = 5.5 V, 3.3 V, or 0,	f = 1 MHz,	Outputs open,	Switch OFF		5.5	7	pF
	S port						3.5	5	
C_{ON}		V_I = 5.5 V, 3.3 V, or 0,	f = 1 MHz,	Outputs open,	Switch ON		10.5	14	pF
r_{on}#		V_{CC} = 3 V	V_I = 1 V,	I_O = 13 mA			3	6	Ω
			V_I = 2 V,	I_O = 26 mA			3	6	
$r_{on(flat)}$‖		V_{CC} = 3.3 V,	V_I = 0 to V_{CC},	I_O = 26 mA			1		Ω

† V_I, V_O, I_I, and I_O refer to I/O pins.
‡ All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.
¶ The I_{OS} test is applicable to only one ON channel at a time. The duration of this test is less than 1 s.
# Measured by the voltage drop between the D and S terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (D or S) terminals.
‖ $r_{on(flat)}$ is the difference of r_{on} in a given channel at specified voltages.

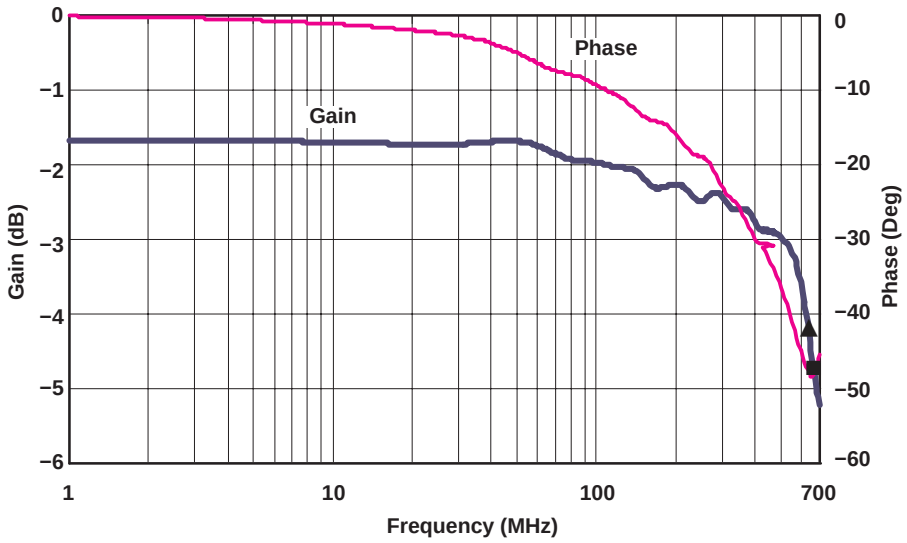
switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V, R_L = 75 Ω, C_L = 20 pF (unless otherwise noted) (see Figures 6 and 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	TYP	MAX	UNIT
$t_{pd(s)}$	IN	D		2	5	ns
t_{ON}	IN or $\overline{EN}$	S		4	7	ns
t_{OFF}	IN or $\overline{EN}$	S		2	7	ns

dynamic characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

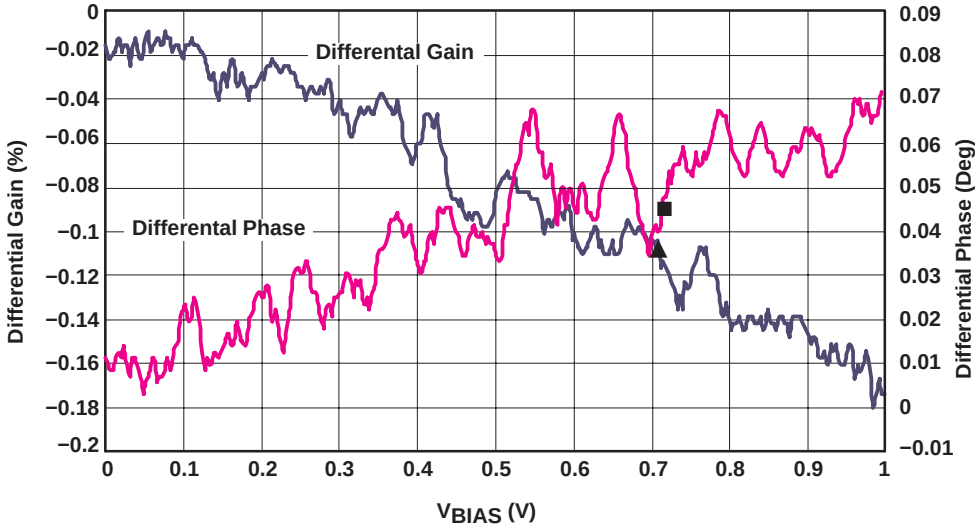
PARAMETER	TEST CONDITIONS				TYP‡	UNIT
D_G☆	R_L = 150 Ω,	f = 3.58 MHz,	See Figure 7		0.2	%
D_P☆	R_L = 150 Ω,	f = 3.58 MHz,	See Figure 7		0.1	°
B_W	R_L = 150 Ω,	See Figure 8			500	MHz
X_{TALK}	R_L = 150 Ω,	f = 10 MHz,	R_{IN} = 10 Ω,	See Figure 9	−80	dB
O_{IRR}	R_L = 150 Ω,	f = 10 MHz,	See Figure 10		−60	dB

‡ All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
☆ D_G and D_P are expressed in absolute magnitude.



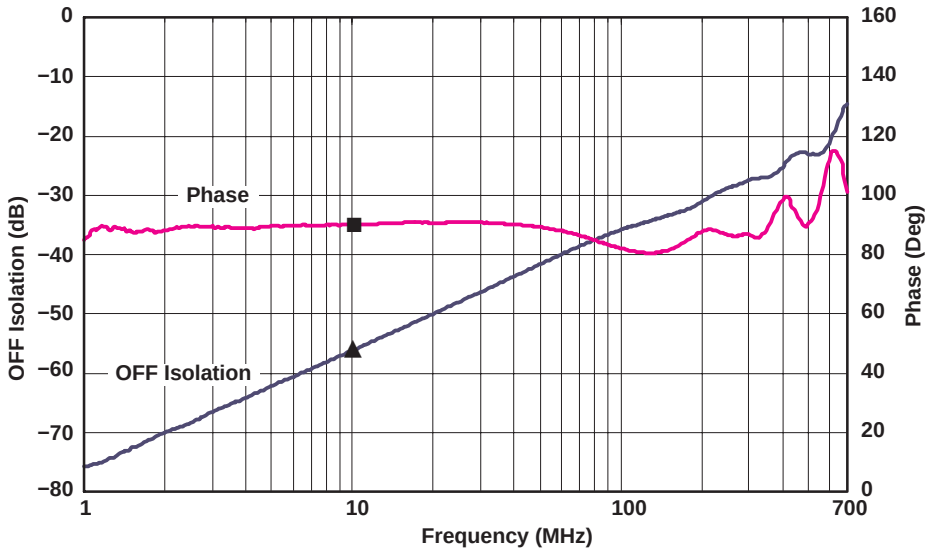
▲ Gain −3 dB at 627 MHz
■ Phase at −3-dB Frequency, −47 Deg

Figure 1. Gain/Phase vs Frequency



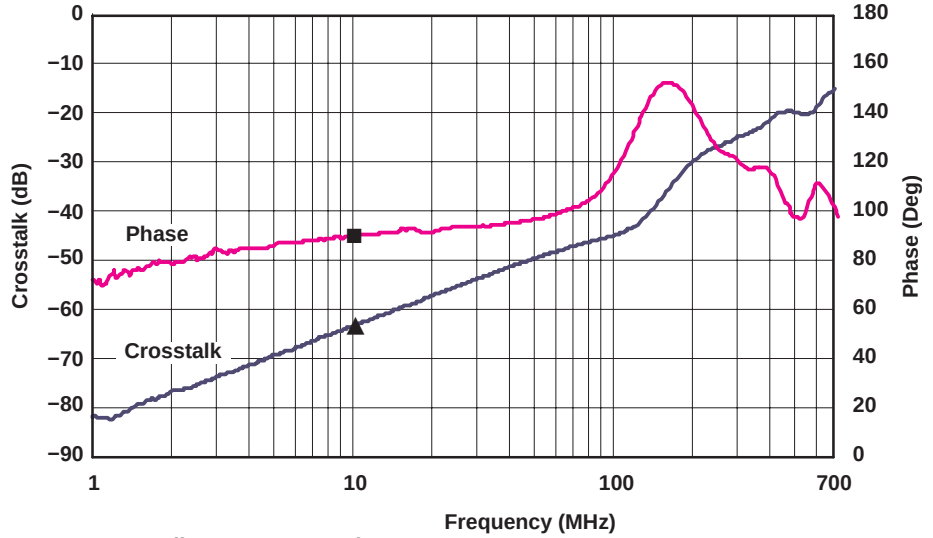
▲ Differential Gain at 0.714 V, −0.11%
■ Differential Phase at 0.714 V, 0.0466 Deg

Figure 2. Differential Gain/Phase vs V_{BIAS}



▲ OFF Isolation at 10 MHz, −56 dB
■ Phase at 10 MHz, 90 Deg

Figure 3. OFF Isolation vs Frequency



▲ Crosstalk at 10 MHz, −63 dB
■ Phase at 10 MHz, 90 Deg

Figure 4. Crosstalk vs Frequency

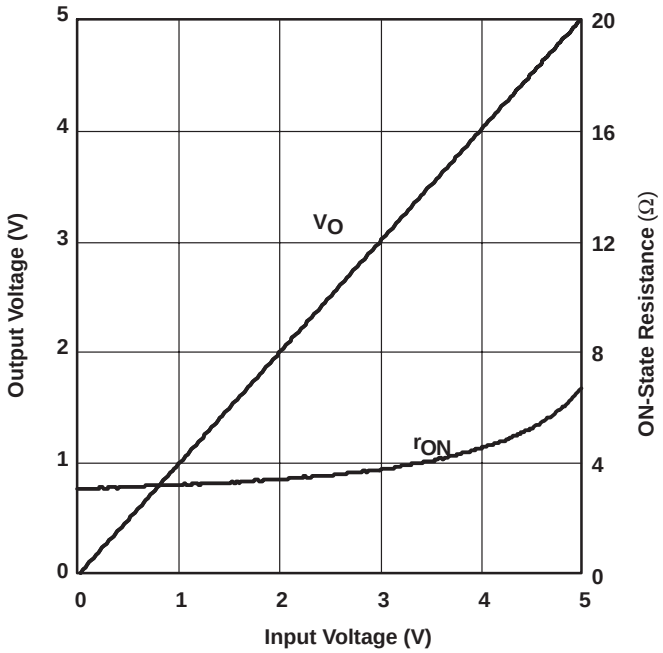
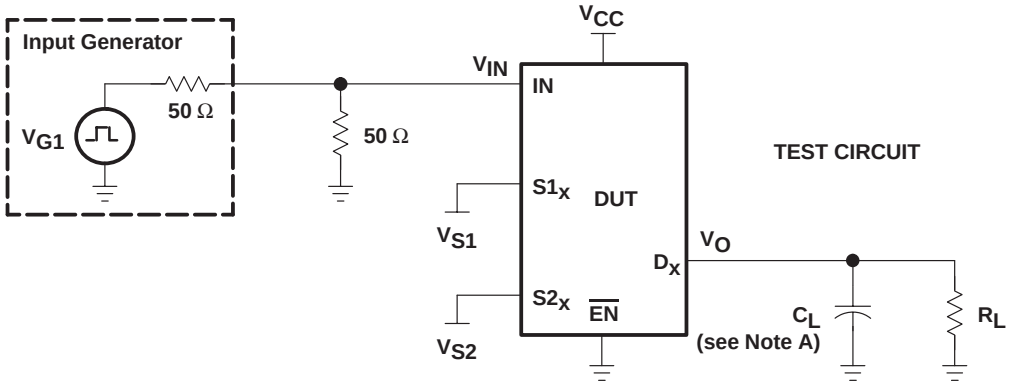
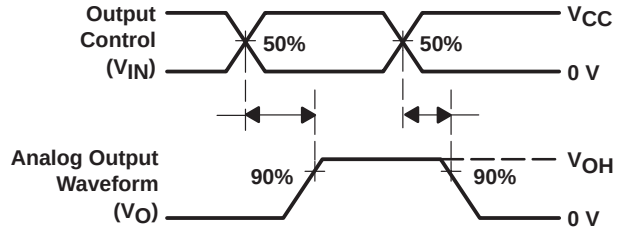


Figure 5. Output Voltage/ON-State Resistance vs Input Voltage

PARAMETER MEASUREMENT INFORMATION



TEST	V_{CC}	R_L	C_L	V_{S1}	V_{S2}
t_{pds}	3.3 V ± 0.3 V	75	20 pF	GND	V_{CC}
	3.3 V ± 0.3 V	75	20 pF	V_{CC}	GND

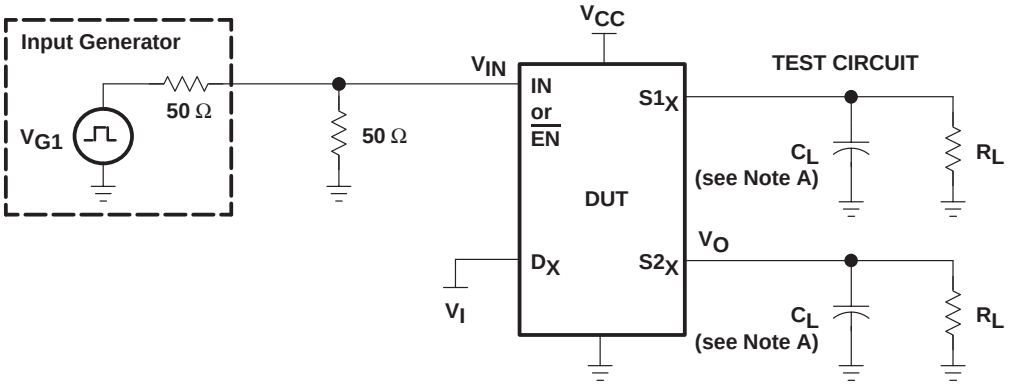


VOLTAGE WAVEFORMS
$t_{pd(s)}$ TIMES

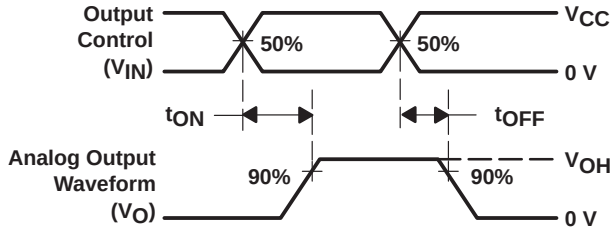
NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time, with one transition per measurement.

Figure 6. Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



TEST	V_{CC}	R_L	C_L	V_I
t_{ON}/t_{OFF}	3.3 V ± 0.3 V	75 Ω	20 pF	V_{CC}

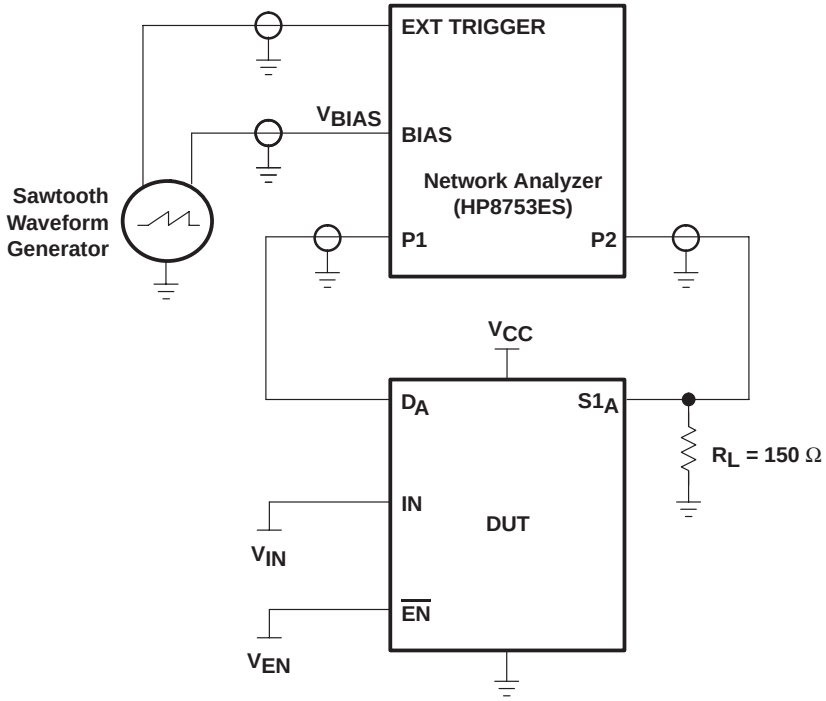


VOLTAGE WAVEFORMS
t_{ON} AND t_{OFF} TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time, with one transition per measurement.

Figure 7. Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



NOTE: For additional information on measurement method, refer to the TI application report, *Measuring Differential Gain and Phase*, literature number SLOA040.

Figure 8. Test Circuit for Differential Gain/Phase Measurement

Differential gain and phase is measured at the output of the ON channel. For example, when V_{IN} = 0, V_{EN} = 0, and D_A is the input, the output is measured at $S1_A$.

HP8753ES setup

Average = 20
RBW = 300 Hz
ST = 1.381 s
P1 = −7 dBM
CW frequency = 3.58 MHz

sawtooth waveform generator setup

V_{BIAS} = 0 to 1 V
Frequency = 0.905 Hz

PARAMETER MEASUREMENT INFORMATION

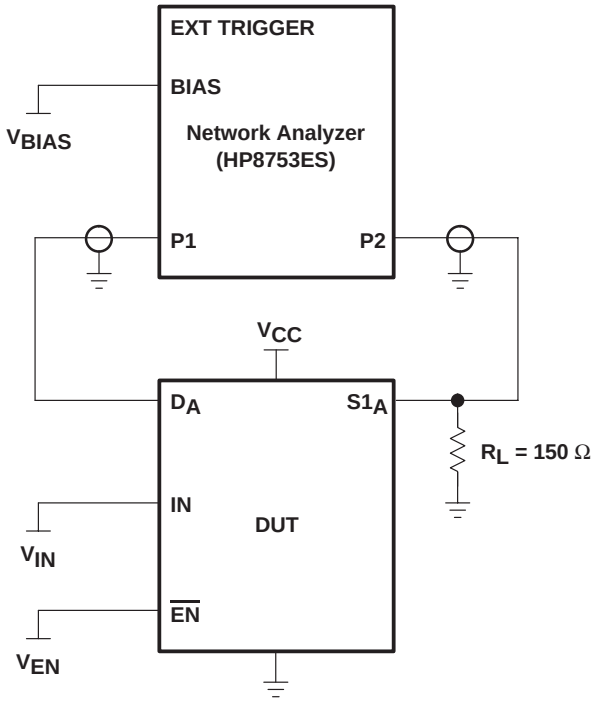


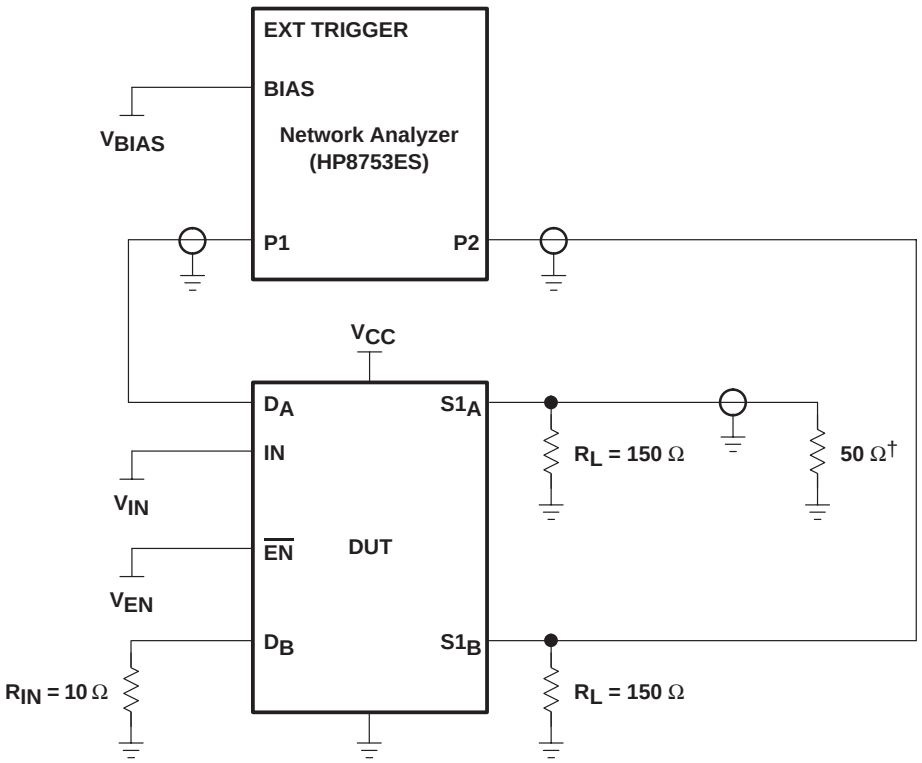
Figure 9. Test Circuit for Frequency Response (B_W)

The frequency response is measured at the output of the ON channel. For example, when V_{IN} = 0, V_{EN} = 0, and D_A is the input, the output is measured at $S1_A$. All unused analog I/O ports are left open.

HP8753ES setup

Average = 4
RBW = 3 kHz
V_{BIAS} = 0.35 V
ST = 2 s
P1 = 0 dBM

PARAMETER MEASUREMENT INFORMATION



† A 50-Ω termination resistor is needed for the network analyzer.

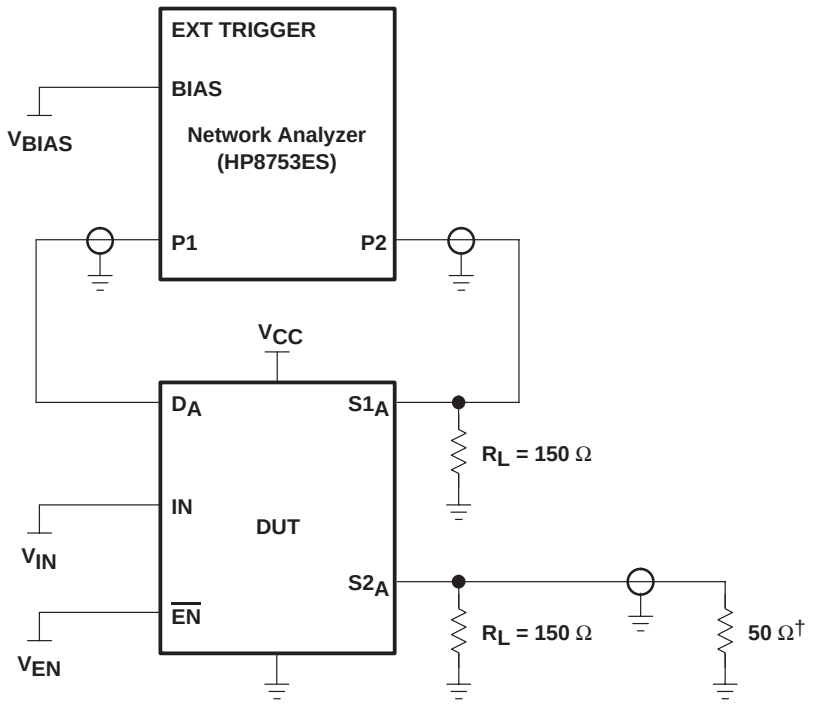
Figure 10. Test Circuit for Crosstalk (X_{TALK})

The crosstalk is measured at the output of the nonadjacent ON channel. For example, when V_{IN} = 0, V_{EN} = 0, and D_A is the input, the output is measured at $S1_B$. All unused analog input (D) ports and output (S) ports are connected to GND through 10-Ω and 50-Ω pulldown resistors, respectively.

HP8753ES setup

Average = 4
RBW = 3 kHz
V_{BIAS} = 0.35 V
ST = 2 s
P1 = 0 dBM

PARAMETER MEASUREMENT INFORMATION



† A 50-Ω termination resistor is needed for the network analyzer.

Figure 11. Test Circuit for OFF Isolation (O_{IRR})

The OFF isolation is measured at the output of the OFF channel. For example, when V_{IN} = V_{CC}, V_{EN} = 0, and D_A is the input, the output is measured at $S1_A$. All unused analog input (D) ports are left open, and output (S) ports are connected to GND through 50-Ω pulldown resistors.

HP8753ES setup

Average = 4
RBW = 3 kHz
V_{BIAS} = 0.35 V
ST = 2 s
P1 = 0 dBM

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS3V340D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V340	Samples
TS3V340DBQR	ACTIVE	SSOP	DBQ	16	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF340	Samples
TS3V340DGVR	ACTIVE	TVSOP	DGV	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF340	Samples
TS3V340DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TS3V340	Samples
TS3V340PW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF340	Samples
TS3V340PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TF340	Samples
TS3V340RGYR	ACTIVE	VQFN	RGY	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TF340	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

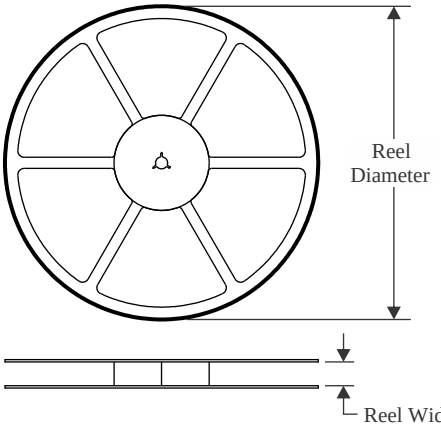
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

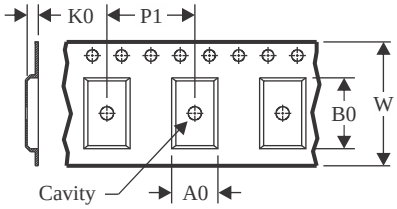
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

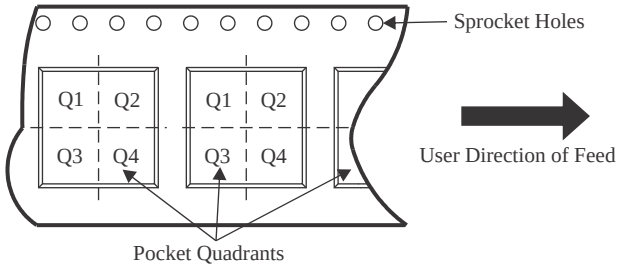


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

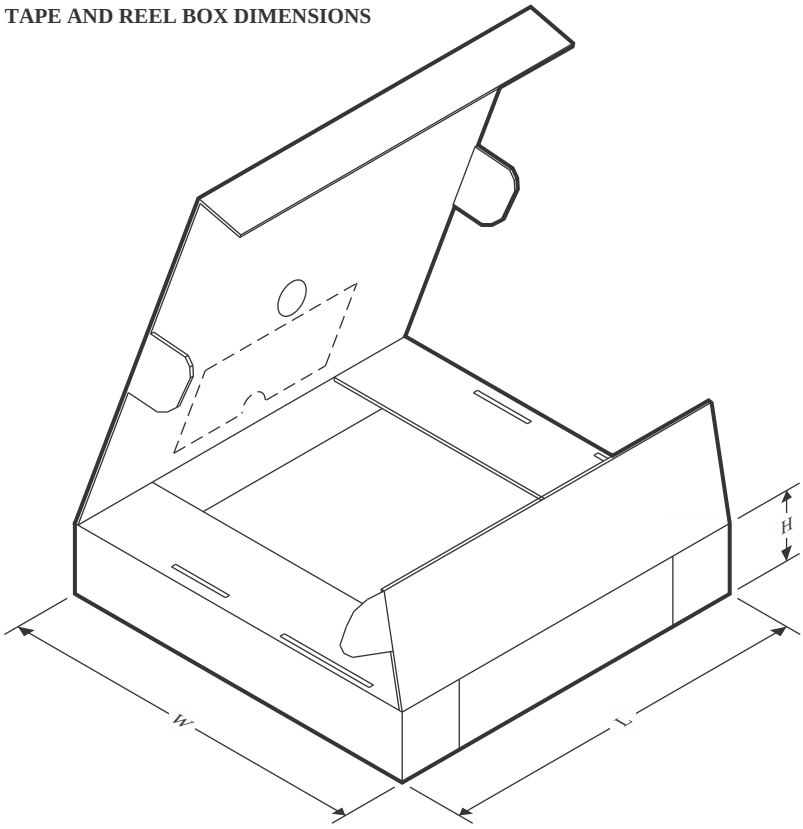
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3V340DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
TS3V340DGVR	TVSOP	DGV	16	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
TS3V340DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TS3V340PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TS3V340RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

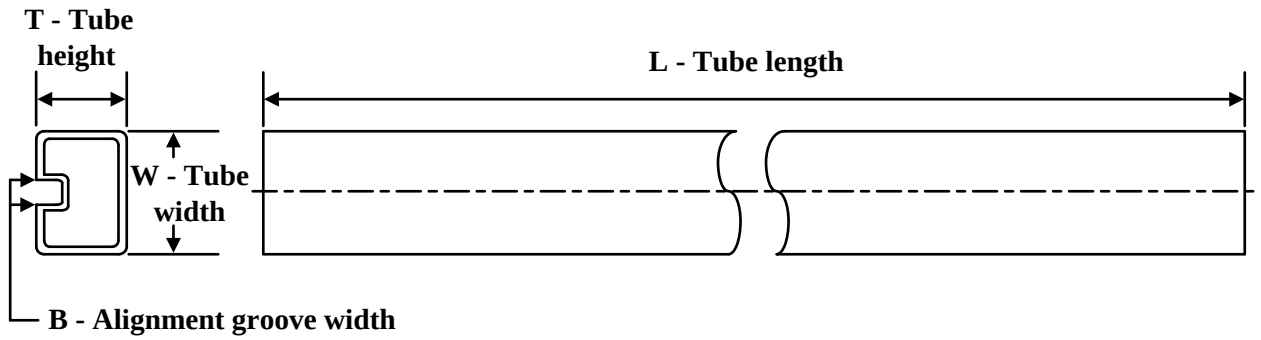
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3V340DBQR	SSOP	DBQ	16	2500	340.5	338.1	20.6
TS3V340DGVR	TVSOP	DGV	16	2000	356.0	356.0	35.0
TS3V340DR	SOIC	D	16	2500	340.5	336.1	32.0
TS3V340PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
TS3V340RGYR	VQFN	RGY	16	3000	356.0	356.0	35.0

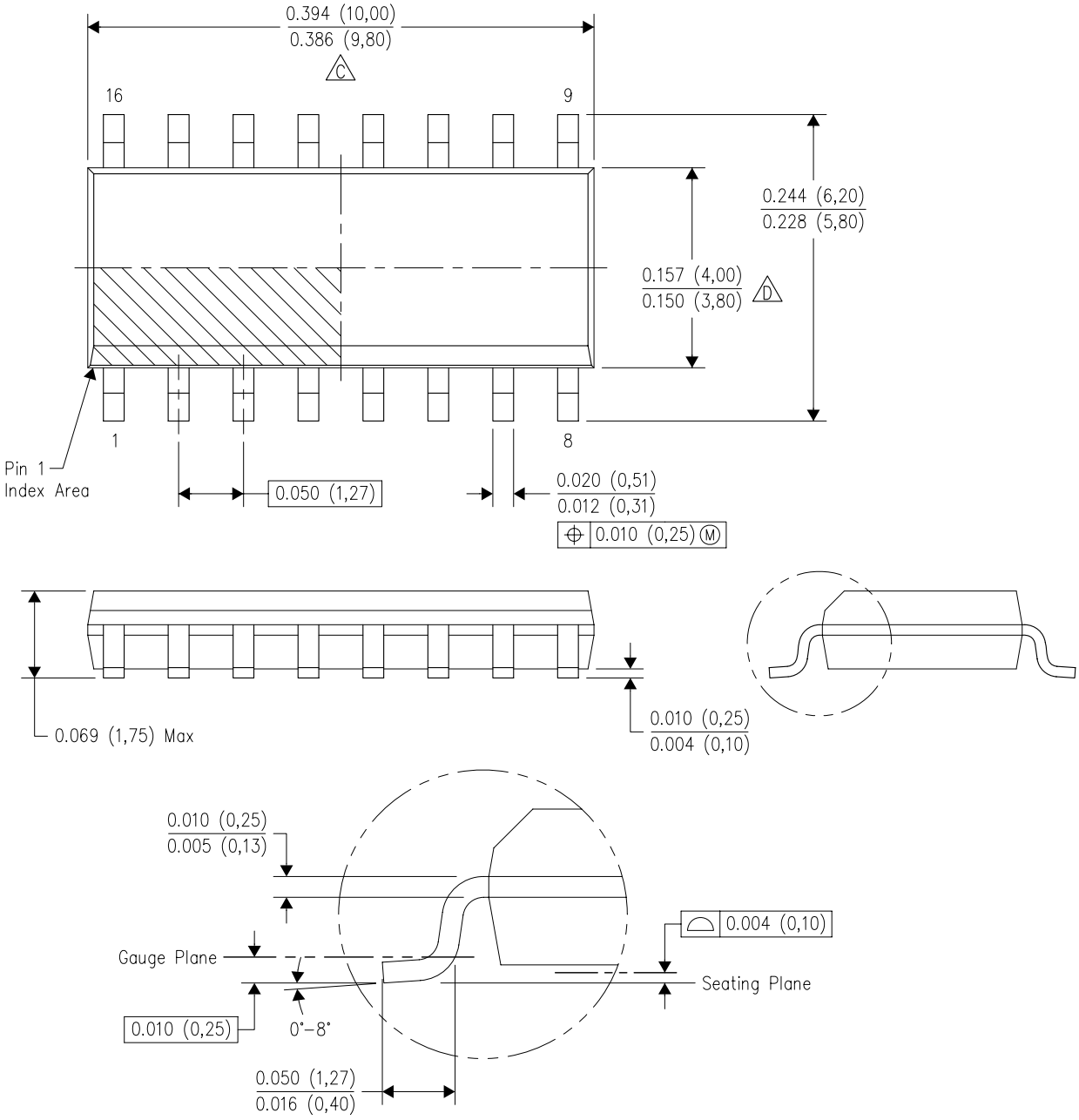
TUBE



*All dimensions are nominal

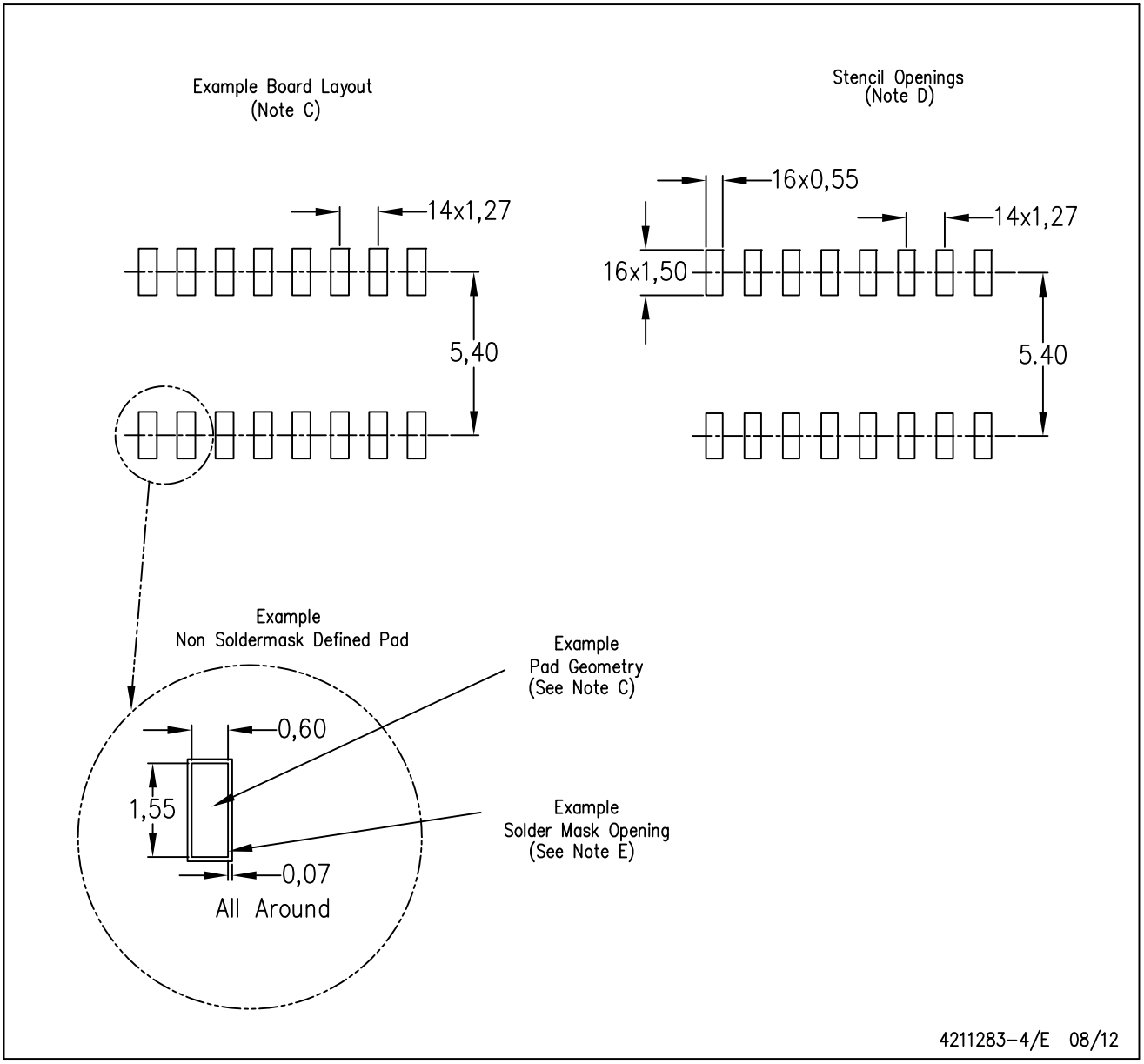
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TS3V340D	D	SOIC	16	40	507	8	3940	4.32
TS3V340PW	PW	TSSOP	16	90	530	10.2	3600	3.5

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



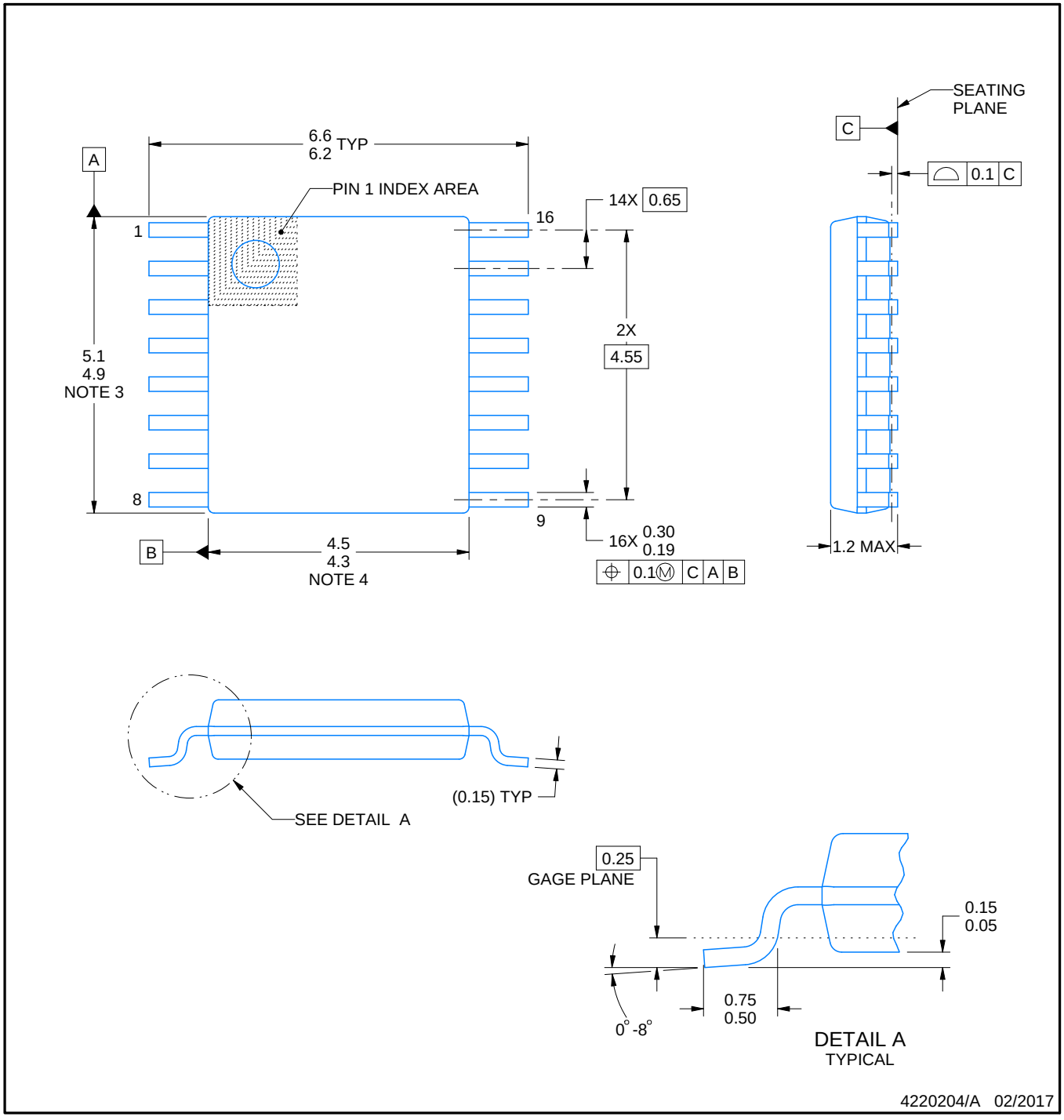
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

PW0016A

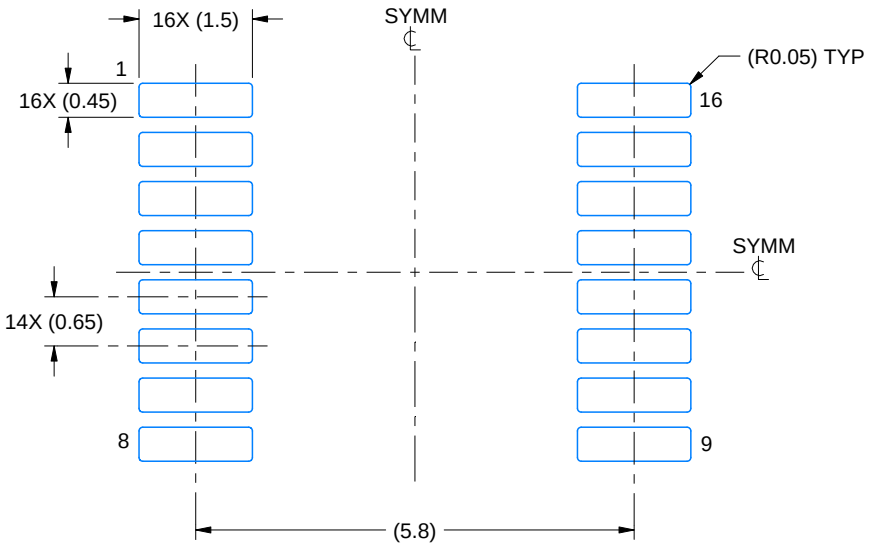
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

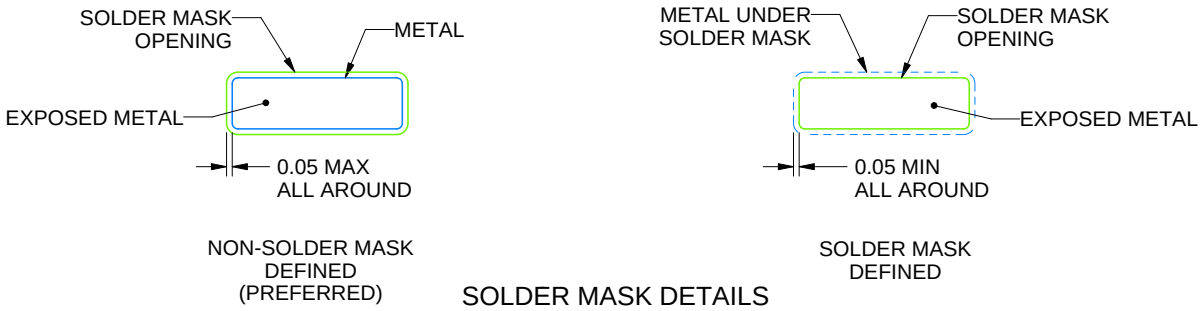


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

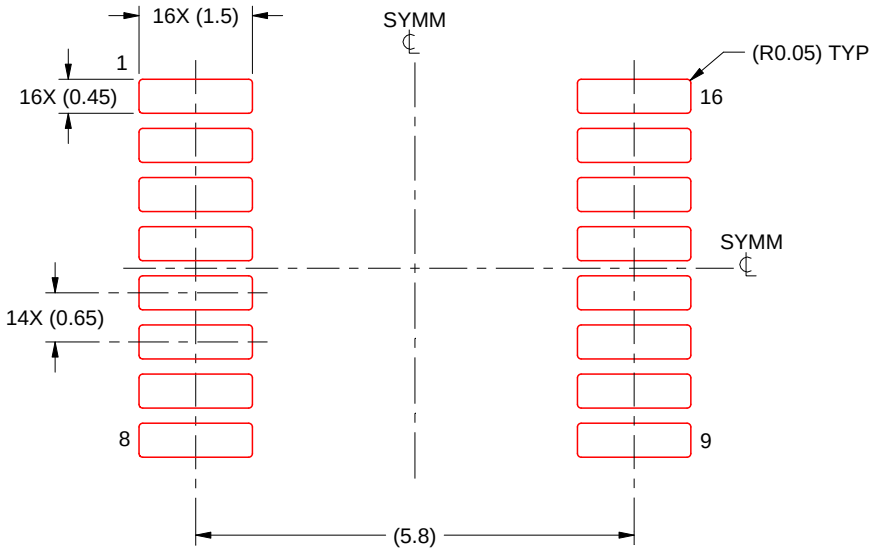


SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

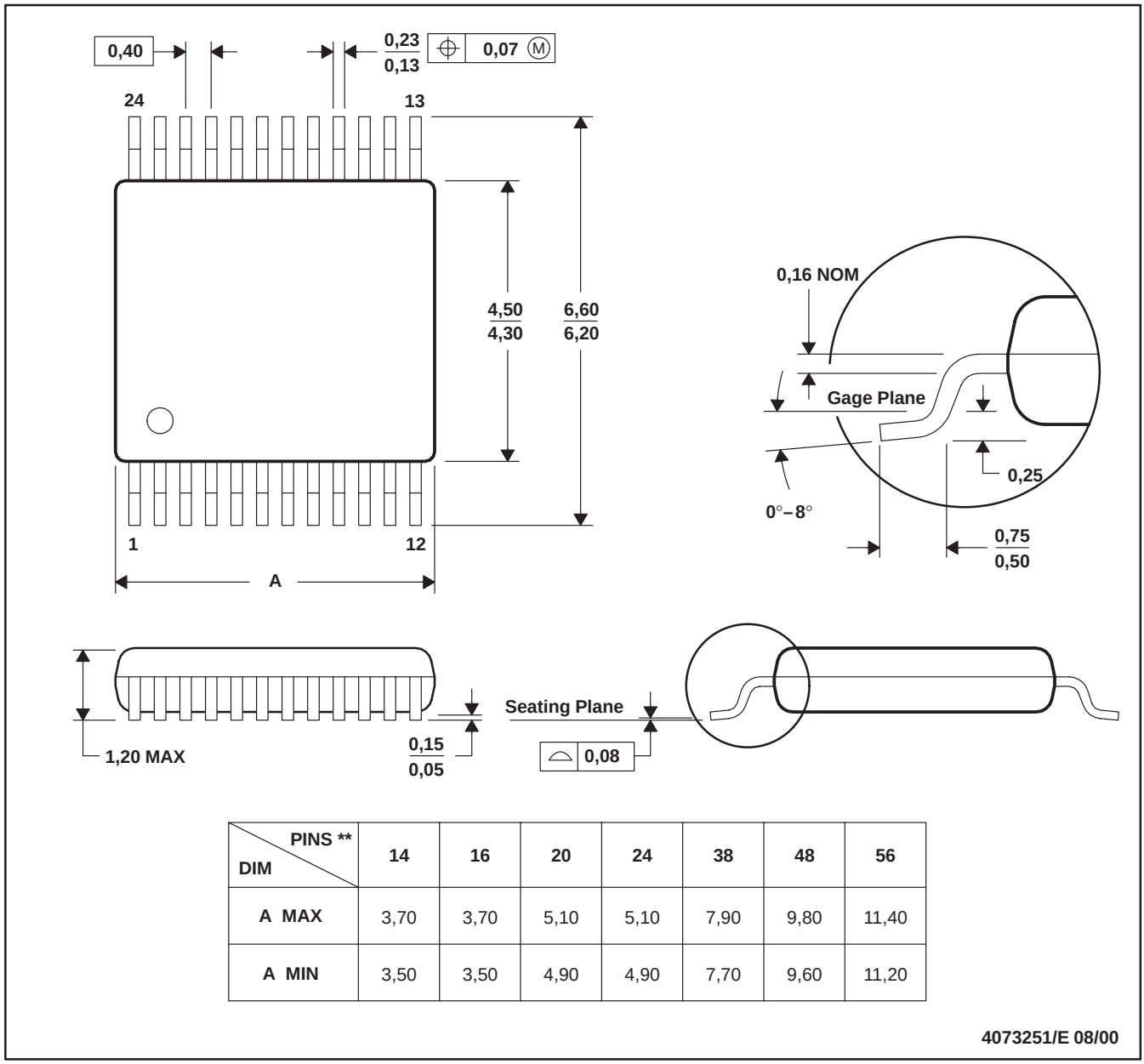
4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DGV (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

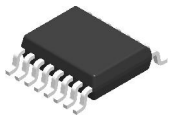
24 PINS SHOWN



DIM \ PINS **	14	16	20	24	38	48	56
A MAX	3,70	3,70	5,10	5,10	7,90	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	7,70	9,60	11,20

4073251/E 08/00

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
D. Falls within JEDEC: 24/48 Pins – MO-153
14/16/20/56 Pins – MO-194

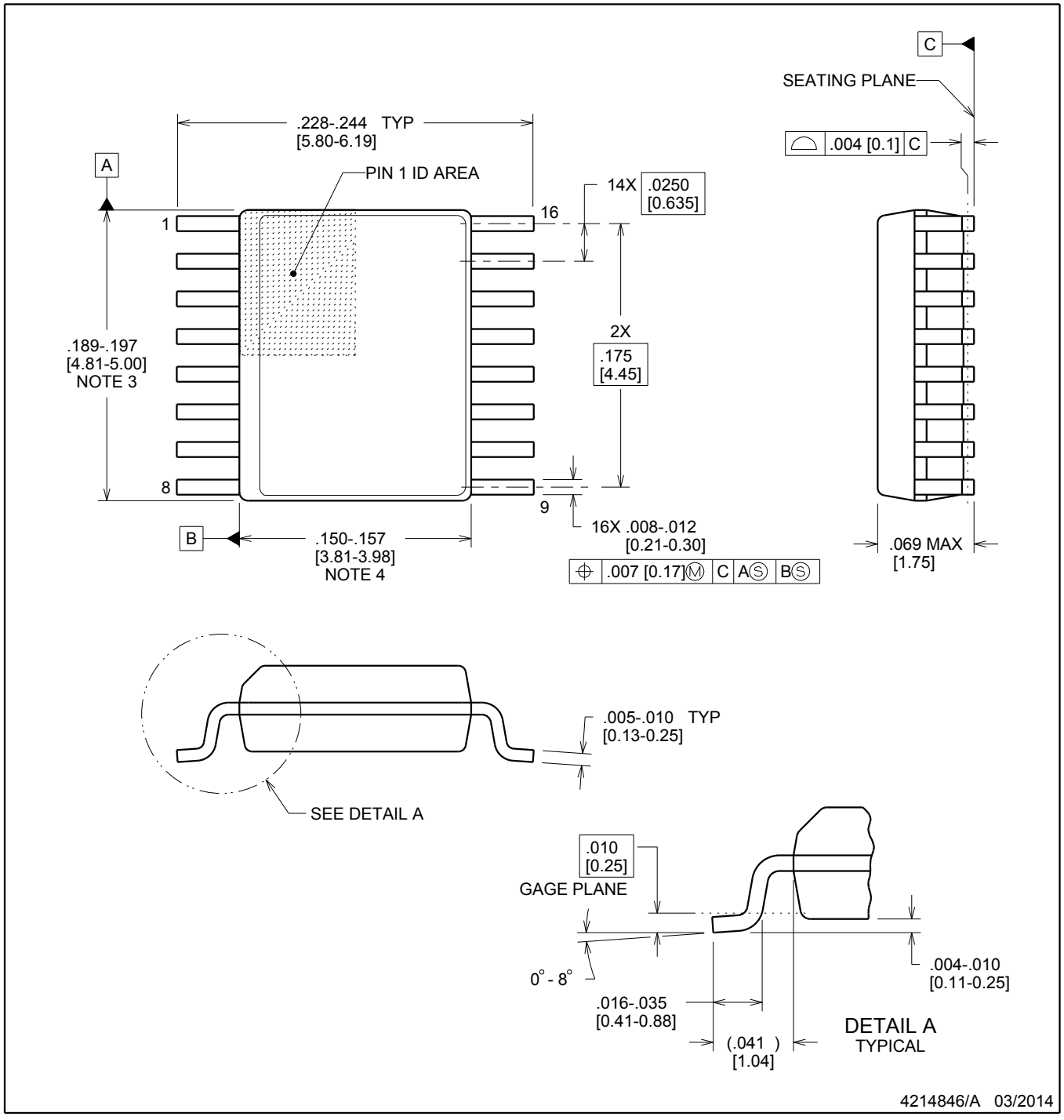


PACKAGE OUTLINE

DBQ0016A

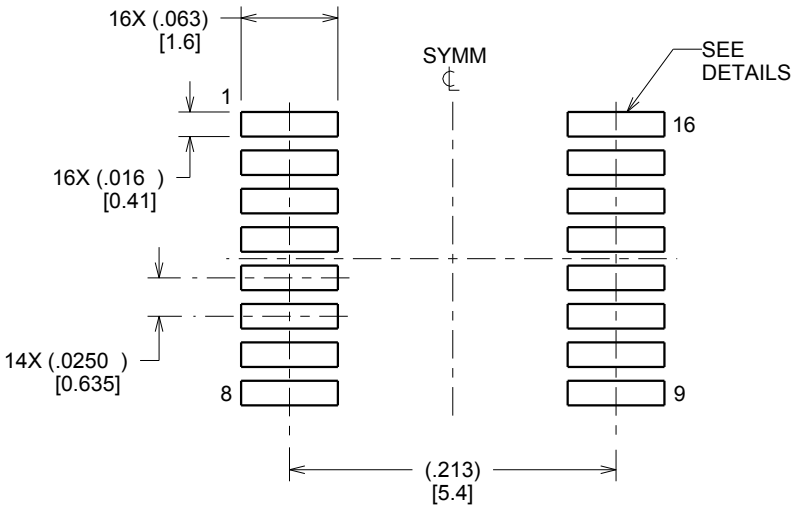
SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE

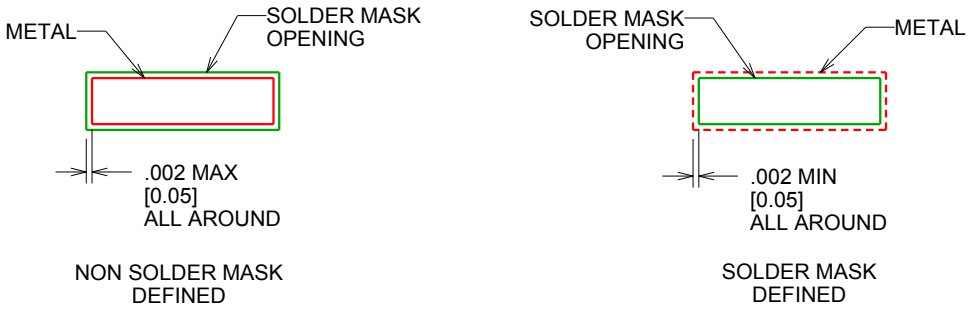


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

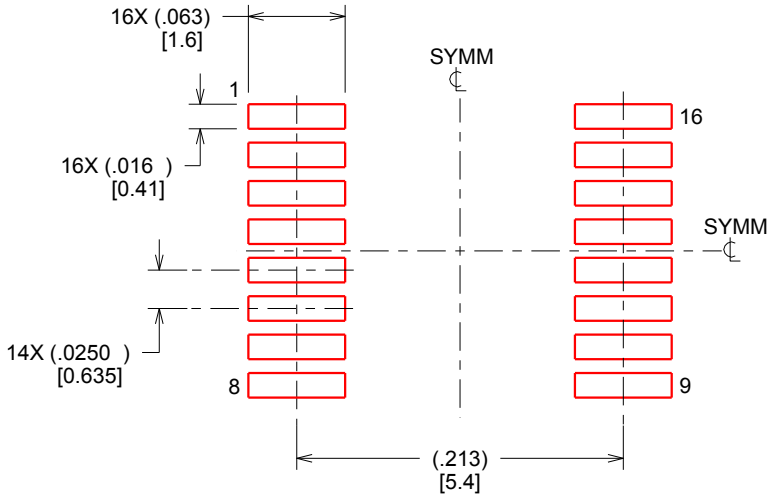
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



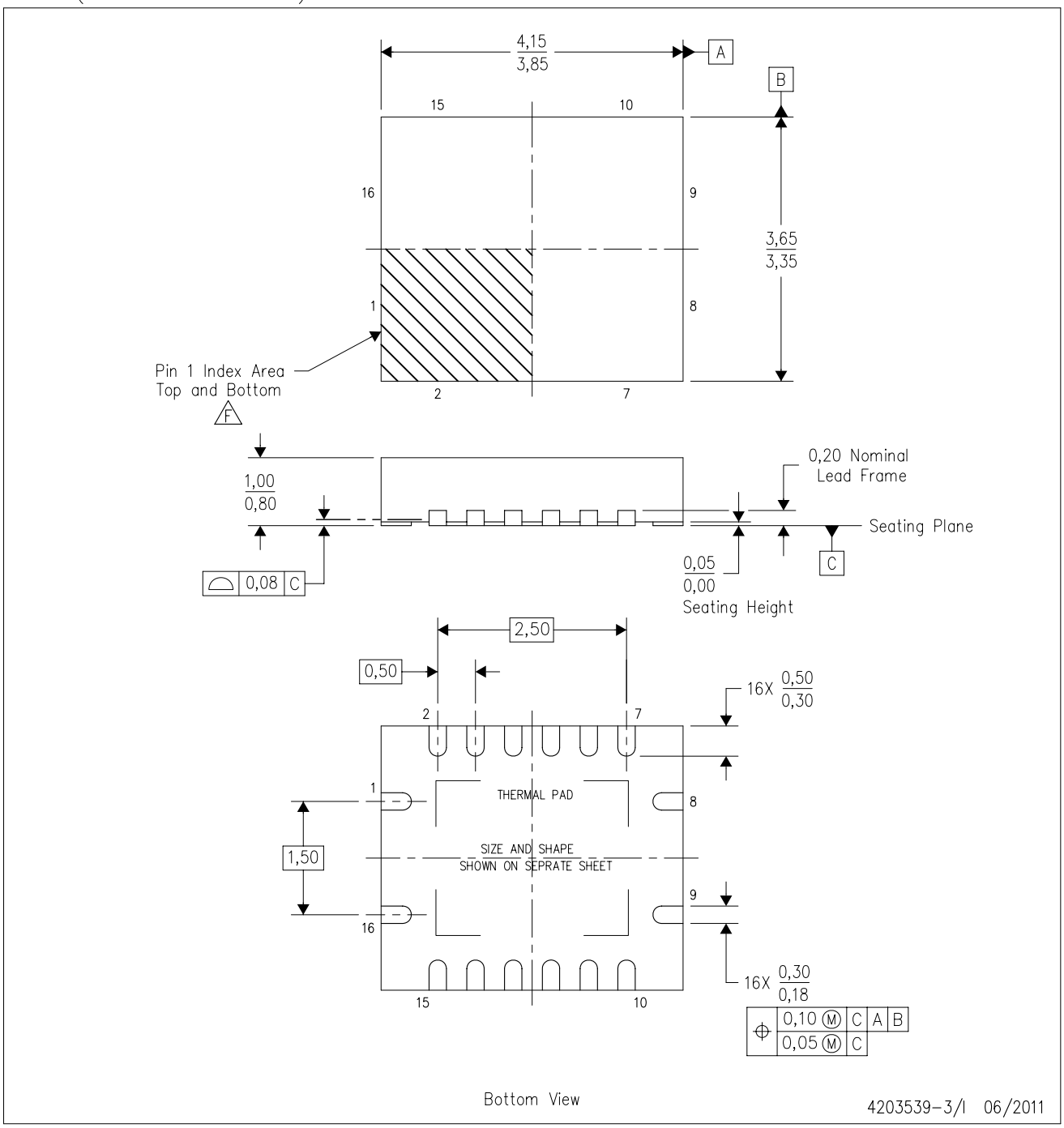
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. QFN (Quad Flatpack No–Lead) package configuration.
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
G. Package complies to JEDEC MO–241 variation BA.

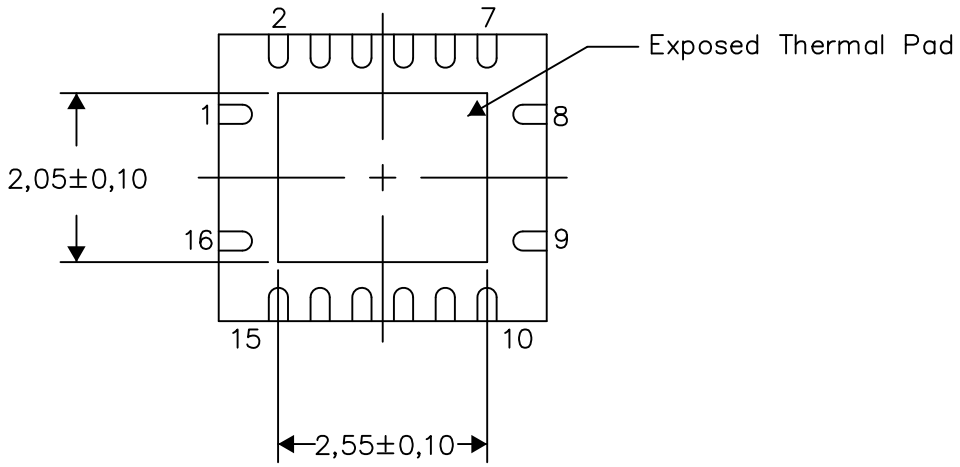
RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



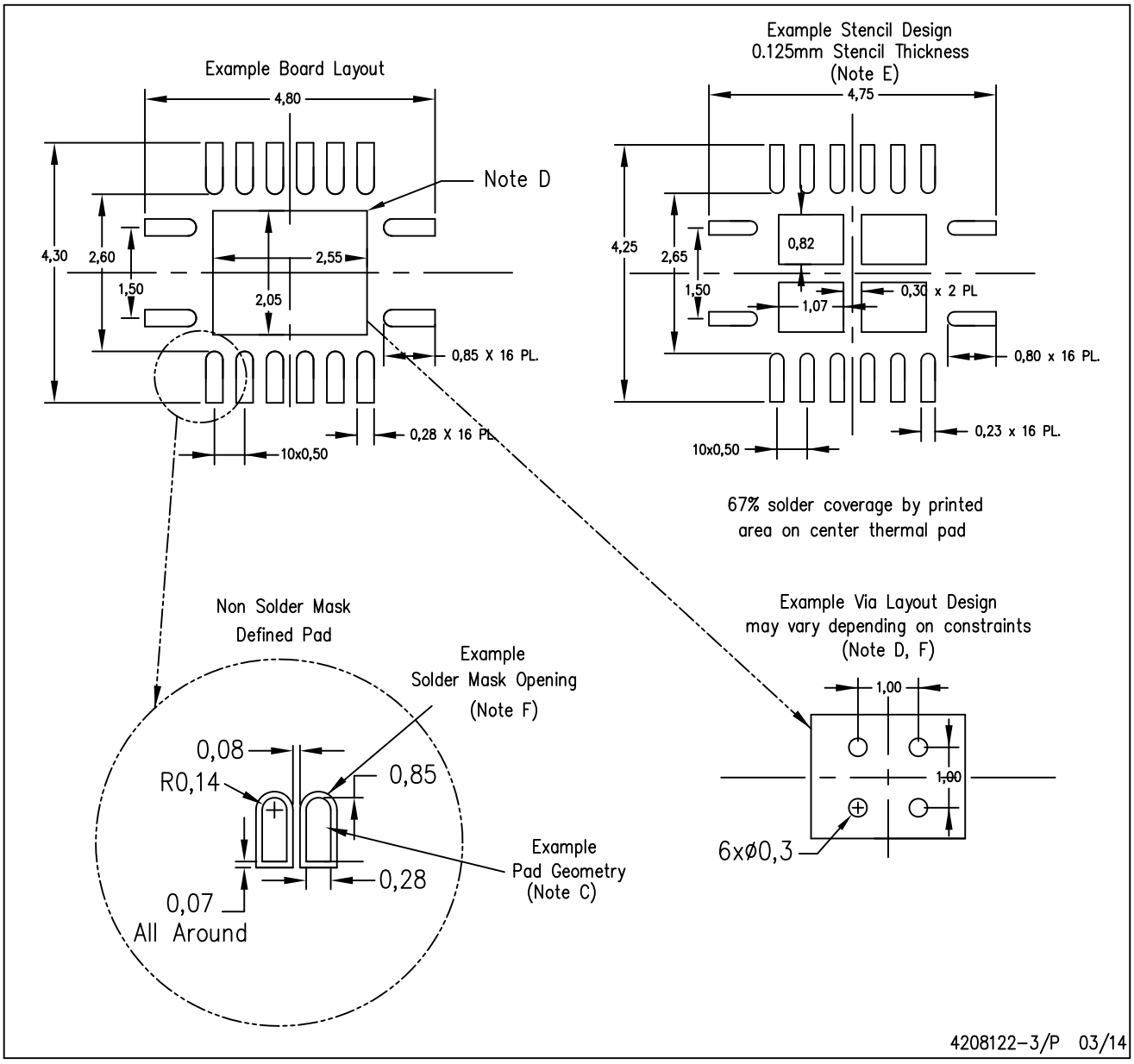
Bottom View

Exposed Thermal Pad Dimensions

4206353–3/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (R–PVQFN–N16) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat–Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

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